

**P-Ch MOSFET** 

# **General Description**

The WSK92P06 is the highest performance trench P-ch MOSFETs with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSK92P06 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

#### **Features**

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

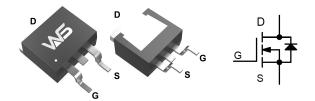
## **Product Summery**

BVDSS	RDSON ID		
-60V	10mΩ	-90A	

# **Applications**

- Power Management
- Load Switch

## **TO-263-2L Pin Configuration**



# **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units	
$V_{DS}$	Drain-Source Voltage	-60	V	
$V_{GS}$	Gate-Source Voltage	±20	V	
I <sub>D</sub> @T <sub>C</sub> =25°C	Continuous Drain Current, -V <sub>GS</sub> @ -10V	-90	Α	
I <sub>D</sub> @T <sub>C</sub> =100℃	Continuous Drain Current, -V <sub>GS</sub> @ -10V	-40	А	
I <sub>DM</sub>	Pulsed Drain Current	-190	А	
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation	96	W	
T <sub>STG</sub>	Storage Temperature Range -55 to 150		$^{\circ}$	
TJ	Operating Junction Temperature Range -55 to 150		${\mathbb C}$	

## **Thermal Data**

Symbol	Parameter	Тур.	Max.	Unit
$R_{ heta JA}$	Thermal Resistance Junction-Ambient		62	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case		1.3	°C/W



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# P-Channel Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =-250uA	-60			V
В	Statia Drain Source On Begintance	V <sub>GS</sub> =-10V , I <sub>D</sub> =-18A		10	14	m()
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-12A		13	18	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS}=V_{DS}$ , $I_D=-250uA$	-1.1	-1.8	-2.5	V
I <sub>DSS</sub>	Drain-Source Leakage Current	$V_{DS}$ =-48V , $V_{GS}$ =0V , $T_J$ =25 $^{\circ}$ C			1	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}=\pm 20V$ , $V_{DS}$ =0V			±100	nA
Qg	Total Gate Charge	Vpc 20 V Vcc 40 V		89		
$Q_{gs}$	Gate-Source Charge	VDS = -30 V, VGS = -10 V, ID = -17A		12		nC
$Q_gd$	Gate-Drain Charge			32		
T <sub>d(on)</sub>	Turn-On Delay Time	VDD = -30 V,		15		
Tr	Rise Time	$RL = 30\Omega$ , $ID = -1$ A,		13		no
$T_{d(off)}$	Turn-Off Delay Time	$V_{GEN} = -10 \text{ V}, R_g = 6\Omega$		110		ns
T <sub>f</sub>	Fall Time			60		
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-30V,V <sub>GS</sub> =0V, f=1.0MHz		4066		
Coss	Output Capacitance			501		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			291		

#### **Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current	T <sub>C</sub> =25 °C			-40	Α
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V , I <sub>S</sub> =-1A , T <sub>J</sub> =25℃			-1.2	V

A: The value of ReJA is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with TA=25°C. The value in any given application depends on the user's specific board design.

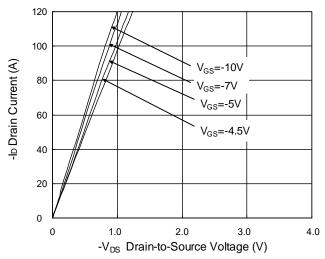
B: Repetitive rating, pulse width limited by junction temperature.

C: The current rating is based on the t≤ 10s junction to ambient thermal resistance rating.



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# P-Channel Typical Characteristics



**Fig.1 Typical Output Characteristics** 

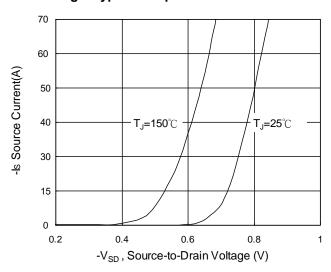


Fig.3 Source Drain Forward Characteristics

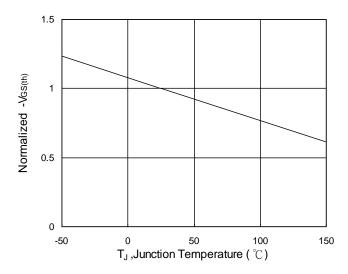


Fig.5 Normalized  $V_{\text{GS(th)}}$  vs  $T_{\text{J}}$ 

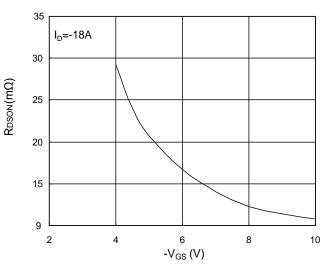


Fig.2 On-Resistance vs G-S Voltage

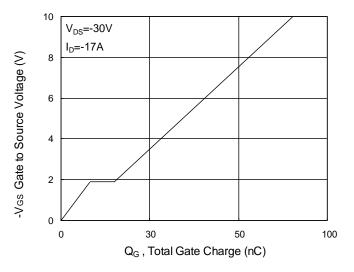


Fig.4 Gate-Charge Characteristics

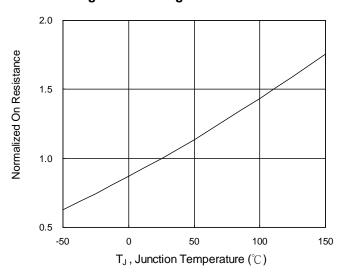


Fig.6 Normalized R<sub>DSON</sub> vs T<sub>J</sub>





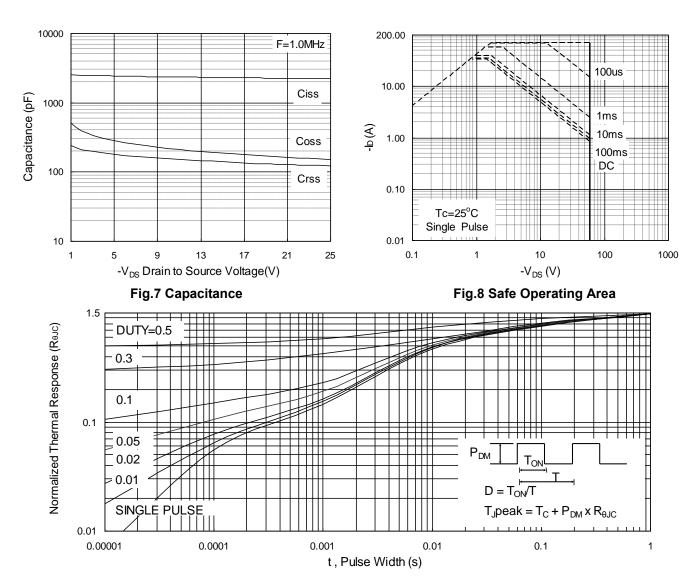


Fig.9 Normalized Maximum Transient Thermal Impedance

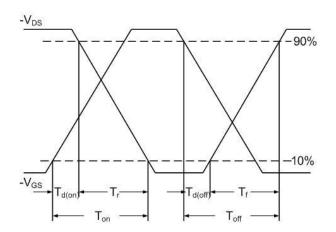


Fig.10 Switching Time Waveform

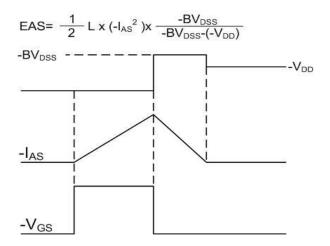


Fig.11 Unclamped Inductive Waveform



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